



## **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- **ESD Protected Up To 2KV**
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.039 grams (approximate)

TSSOP-8L



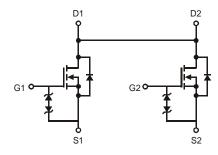


**TOP VIEW** 





Top View Pin Configuration



Internal Schematic

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                    |                 |                                | Symbol         | Value        | Unit |
|-----------------------------------|-----------------|--------------------------------|----------------|--------------|------|
| Drain-Source Voltage              |                 |                                | $V_{DSS}$      | 20           | V    |
| Gate-Source Voltage               |                 | V <sub>GSS</sub>               | ±8             | V            |      |
| Continuous Drain Current (Note 3) | Steady<br>State | $T_A = 25$ °C<br>$T_A = 85$ °C | I <sub>D</sub> | 8.58<br>5.73 | А    |
| Pulsed Drain Current (Note 4)     |                 | I <sub>DM</sub>                | 36             | А            |      |

#### **Thermal Characteristics**

| Characteristic  | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 3)  | P <sub>D</sub>                    | 0.88        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 3) | $R_{\theta JA}$                   | 141.57      | °C/W |
| Operating and Storage Temperature Range                                 | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

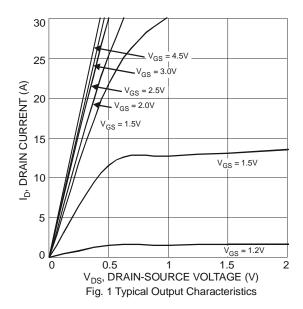


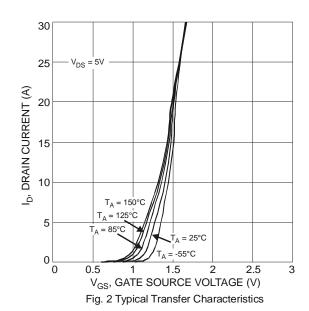
### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic  | Symbol               | Min | Тур   | Max  | Unit | Test Condition  |  |
|---|----------------------|-----|-------|------|------|---|--|
| OFF CHARACTERISTICS (Note 5)                          |                      |     |       |      |      |   |  |
| Drain-Source Breakdown Voltage                        | BV <sub>DSS</sub>    | 20  | -     | -    | V    | $V_{GS} = 0V, I_D = 250\mu A$   |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C | I <sub>DSS</sub>     | -   | -     | 1.0  | μΑ   | $V_{DS} = 20V, V_{GS} = 0V$   |  |
| Gate-Source Leakage                                   | $I_{GSS}$            | -   | -     | ±10  | μΑ   | $V_{GS} = \pm 8V$ , $V_{DS} = 0V$                                       |  |
| ON CHARACTERISTICS (Note 5)                           |                      |     |       |      |      |   |  |
| Gate Threshold Voltage                                | V <sub>GS(th)</sub>  | 0.4 | 0.72  | 1.0  | V    | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                                    |  |
| Static Drain-Source On-Resistance                     |                      | _   | 11    | 14.5 | mΩ   | $V_{GS} = 4.5V, I_D = 9.4A$   |  |
| Static Drain-Source On-Nesistance                     | R <sub>DS</sub> (ON) | -   | 13    | 16.5 |      | $V_{GS} = 2.5V, I_D = 8.3A$   |  |
| Forward Transfer Admittance                           | Y <sub>fs</sub>      | -   | 19    | ı    | S    | $V_{DS} = 5V, I_{D} = 9.4A$   |  |
| Diode Forward Voltage                                 | $V_{SD}$             | -   | 0.65  | 1.2  | V    | $V_{GS} = 0V, I_{S} = 1.3A$   |  |
| DYNAMIC CHARACTERISTICS (Note 6)                      |                      |     |       |      |      |   |  |
| Input Capacitance                                     | C <sub>iss</sub>     | -   | 1495  | -    | pF   | \/ 40\/ \/ 0\/  |  |
| Output Capacitance                                    | Coss                 | -   | 161   | -    | pF   | $V_{DS} = 10V, V_{GS} = 0V,$<br>f = 1.0MHz                              |  |
| Reverse Transfer Capacitance                          | $C_{rss}$            | -   | 152   | -    | pF   | T = 1.0WHZ  |  |
| Gate Resistance                                       | $R_g$                | -   | 1.42  | ı    | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                              |  |
| Total Gate Charge                                     | $Q_g$                | -   | 16.5  | ı    | nC   | V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V,<br>I <sub>D</sub> = 9.4A |  |
| Gate-Source Charge                                    | $Q_{gs}$             | -   | 2.5   | i    | nC   |   |  |
| Gate-Drain Charge                                     | $Q_{gd}$             | -   | 3.2   | •    | nC   |   |  |
| Turn-On Delay Time                                    | t <sub>D(on)</sub>   | -   | 10.39 | i    | ns   |   |  |
| Turn-On Rise Time                                     | t <sub>r</sub>       | -   | 11.66 | i    | ns   | $V_{DD} = 10V, V_{GS} = 4.5V,$  |  |
| Turn-Off Delay Time                                   | t <sub>D(off)</sub>  | -   | 59.38 | ·    | ns   | $R_{GEN} = 6\Omega, I_D = 1A, R_1 = 10\Omega$                           |  |
| Turn-Off Fall Time                                    | t <sub>f</sub>       | -   | 16.27 | ı    | ns   |   |  |

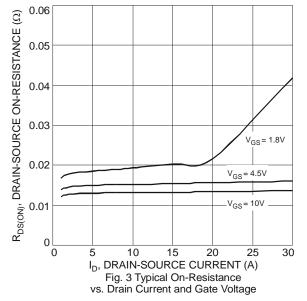
otes: 5. Short duration pulse test used to minimize self-heating effect.

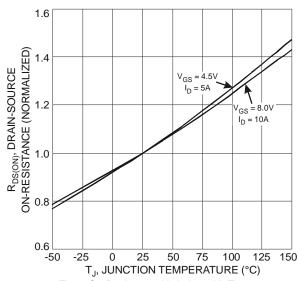
6. Guaranteed by design. Not subject to production testing.

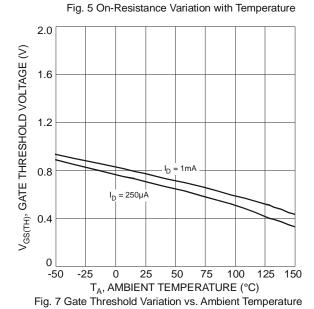












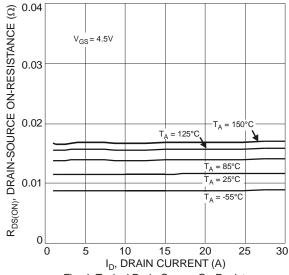
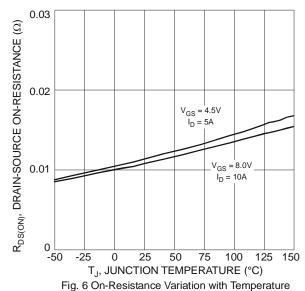
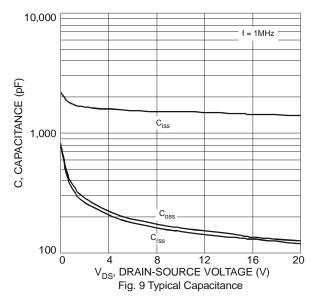


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature



20 16 17 T<sub>A</sub> = 25°C T<sub>A</sub> =





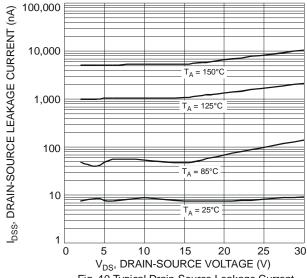
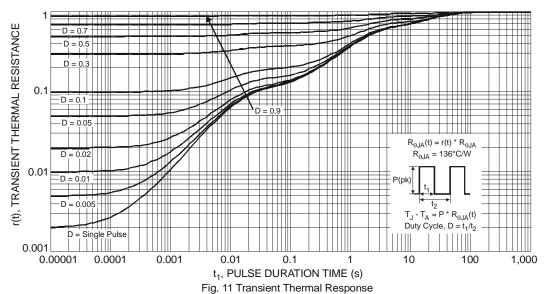


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

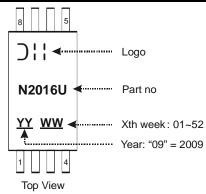


### Ordering Information (Note 7)

| Part Number   | Case     | Packaging          |
|---------------|----------|--------------------|
| DMN2016UTS-13 | TSSOP-8L | 2500 / Tape & Reel |

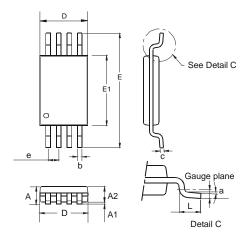
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



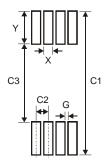


## **Package Outline Dimensions**



| TSSOP-8L             |       |       |       |  |
|----------------------|-------|-------|-------|--|
| Dim                  | Min   | Max   | Тур   |  |
| а                    | 0.09  | -     | -     |  |
| Α                    | _     | 1.20  | _     |  |
| A1                   | 0.05  | 0.15  | -     |  |
| A2                   | 0.825 | 1.025 | 0.925 |  |
| b                    | 0.19  | 0.30  | _     |  |
| C                    | 0.09  | 0.20  | _     |  |
| D                    | 2.90  | 3.10  | 3.025 |  |
| е                    | _     | _     | 0.65  |  |
| Е                    | _     | _     | 6.40  |  |
| E1                   | 4.30  | 4.50  | 4.425 |  |
| L                    | 0.45  | 0.75  | 0.60  |  |
| All Dimensions in mm |       |       |       |  |

# **Suggested Pad Layout**



| <b>Dimensions</b> | Value (in mm) |
|-------------------|---------------|
| Х                 | 0.45          |
| Y                 | 1.78          |
| C1                | 7.72          |
| C2                | 0.65          |
| C3                | 4.16          |
| G                 | 0.20          |



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